查询"MMBT2222AT"供应商



MMBT2222AT

| NPN | Epitaxial | Silicon | Transistor |
|-----|-----------|---------|------------|
|-----|-----------|---------|------------|

Features

- General purpose amplifier transistor.
- Ultra-Small Surface Mount Package for all types.
- General purpose switching & amplification application



September 2008

B Marking : A02 SOT-523F

Absolute Maximum Ratings T_a = 25°C unless otherwise noted

| Symbol | Parameter | Value | Unit |
|------------------|---------------------------|-----------|------|
| V _{CBO} | Collector-Base Voltage | 75 | V |
| V _{CEO} | Collector-Emitter Voltage | 40 | V |
| V _{EBO} | Emitter-Base Voltage | 6 | V |
| с | Collector Current | 600 | mA |
| Гј | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature Range | -55 ~ 150 | °C |

* 1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics* T_=25°C unless otherwise noted

| Symbol | Parameter | Max | Unit |
|----------------|---|-----|------|
| P _C | Collector Power Dissipation, by $R_{\theta JA}$ | 250 | mW |
| R_{\thetaJA} | Thermal Resistance, Junction to Ambient | 500 | °C/W |

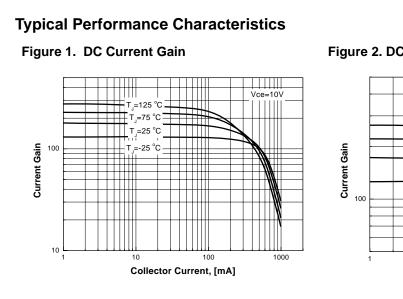
* Minimum land pad.

Electrical Characteristics* T_a=25°C unless otherwise noted

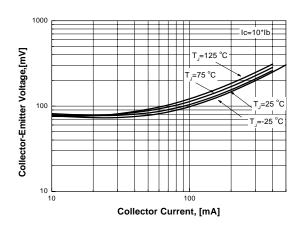
| Symbol | Parameter | Test Condition | Min. | Max. | Unit |
|-----------------------|--------------------------------------|--|-----------------------|------------|--------|
| BV _{CBO} | Collector-Base Breakdown Voltage | $I_{C} = 10 \mu A, I_{E} = 0$ | 75 | | V |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | $I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$ | 40 | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_{\rm E} = 10\mu A, I_{\rm C} = 0$ | 6 | | V |
| ICEX | Collector Cut-off Current | $V_{CE} = 60V, V_{EB(OFF)} = 3V$ | | 10 | nA |
| h _{FE} | DC Current Gain | | 35 50 75 100 | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | $I_{C} = 150$ mA, $I_{B} = 15$ mA $I_{C} = 500$ mA, $I_{B} = 50$ mA | | 0.3 1.0 | V V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA | 0.6 | 1.2 2.0 | V V |
| f _T | Current Gain Bandwidth Product | V _{CE} = 20V, I _C = 20mA, f = 100MHz | 300 | | MHz |
| C _{ob} | Output Capacitance | $V_{CB} = 10V, I_E = 0, f = 1MHz$ | | 8 | pF |
| C _{ib} | Input Capacitance | $V_{EB} = 0.5V, I_{C} = 0, f = 1MHz$ | | 30 | pF |
| t _d | Delay Time | $V_{CC} = 30V, I_{C} = 150mA$ | | 10 | ns |
| t _r | Rise Time | I _{B1} =- I _{B2} = 15mA | | 25 | ns |
| t _s | Storage Time | | | 225 | ns |
| t _f | Fall Time | | | 60 | ns |

* DC Item are tested by Pulse Test : Pulse Width ${\leq}300 us,$ Duty Cycle ${\leq}2\%$

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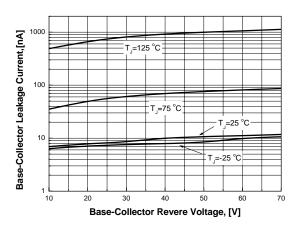
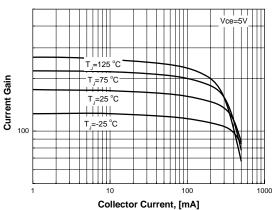


Figure 2. DC Current Gain





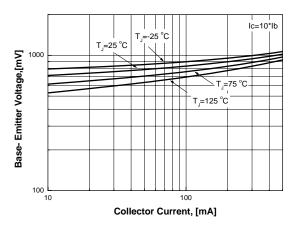
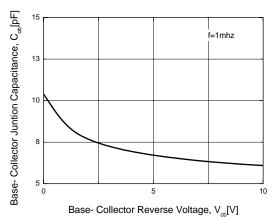
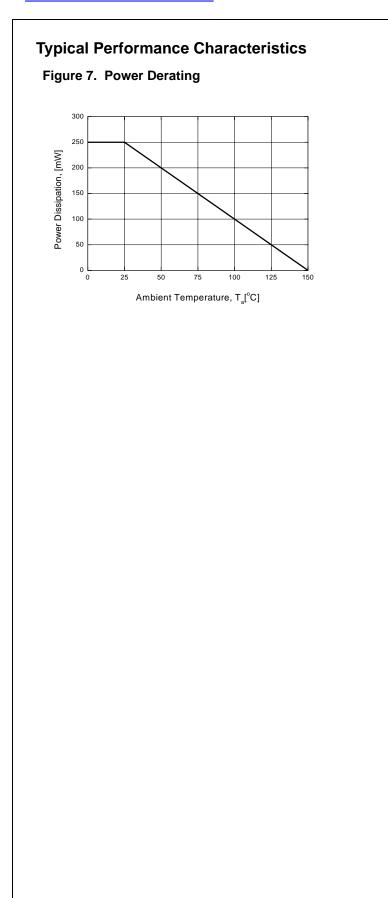


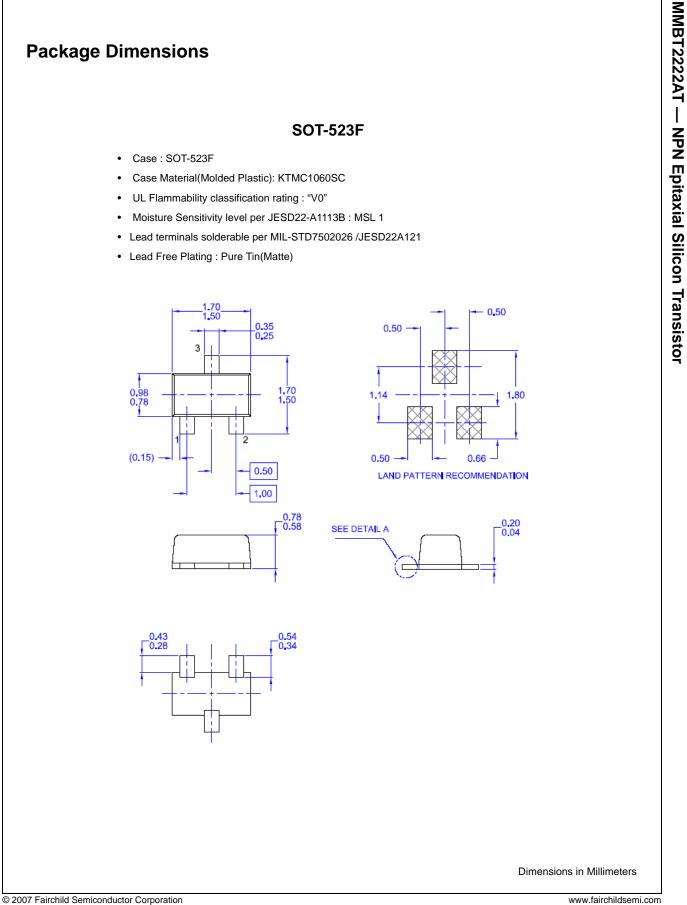
Figure 6. Collector-Base Capapcitance



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